

U.S. Serial No. 09/501,114

## PATENTS

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: )  
Tzeng ) Group Art Unit: 1762  
Serial No: 09/501,114 ) Examiner: Markham, W.  
Filed: February 10, 2000 ) Docket No.: A029 1080  
For: Method of Plasma Enhanced )  
Chemical Vapor Deposition of )  
Diamond )

AMENDMENT UNDER 37 C.F.R. §1.113

Assistant Commissioner For Patents  
Box Non-Fee Amendment  
Washington, D.C. 20231

Dear Sir:

In response to the office action dated January 3, 2002, please amend the subject application as follows.

IN THE SPECIFICATION

Please substitute the following paragraph for the paragraph beginning at line 18 of page 10 and ending at line 4 of page 11 of the specification.

Figure 1 generally illustrates the plasma enhanced chemical vapor deposition system utilized in performing the method of the present invention. As illustrated in Fig. 1, the precursor 5 is fed from a precursor container 4 by a conduit 6, such as a TEFLON (polytetrafluoroethylene) or metal tubing, through a liquid flow controller 7, such as a needle valve, to an inlet 2 of reactor